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PATENT
0941-0784P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: KING, Wei-Shang Conf.: 4930
Appl. No.: 10/024,274 Group: 10/024,274
Filed: December 17, 2001 Examiner: 2823
For: SEMICONDUCTOR STRUCTURE CONTAINING FIELD
OXIDE AND METHOD FOR FABRICATION THE
SAME

LARGE ENTITY TRANSMITTAL FORM

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

December 17, 2004

Sir:


Transmitted herewith is a Reply to Restriction/Election Requirement in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ Petition for _____ (____) month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ A check in the amount of \$0.00 is enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. A triplicate copy of this sheet is attached.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By 
Joe McKinney Muncy, #32,334

KM/asc
0941-0784P

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Attachment(s)



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For: SEMICONDUCTOR STRUCTURE CONTAINING
FIELD OXIDE AND METHOD FOR FABRICATION
THE SAME

REPLY TO RESTRICTION REQUIREMENT

Assistant Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

December 17, 2004

Sir:

Responsive to the Office Action dated November 17, 2004, the following election and remarks are respectfully submitted in connection with the above-identified application.

REMARKS

Claims 1-17 are now pending in the present application.

The Examiner has given the following Restriction Requirement:

Group I, claims 1-10, drawn to a method for fabricating a semiconductor device, classified in class 257, subclass 192+; and

Group II, claims 11-17, drawn to a method for fabricating a semiconductor device, classified in class 438, subclass 197+.

In response to this requirement, Applicants hereby elect Group II, claims 11-17 drawn to a method for fabricating a semiconductor